

# **BSS84AKW**

# 50 V, 150 mA P-channel Trench MOSFET Rev. 1 — 23 May 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- AEC-Q101 qualified

#### 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-50	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	[1]	-	-	-150	mΑ
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_{D}$ = -100 mA; $T_{j}$ = 25 °C		-	4.5	7.5	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	3	D
3	D	drain	1 ☐ ☐ 2 SOT323 (SC-70)	G S Sym146

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS84AKW	SC-70	plastic surface-mounted package; 3 leads	SOT323		

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BSS84AKW	%VT

[1] % = placeholder for manufacturing site code

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>i</sub> = 25 °C		-	-50	V
gate-source voltage	_ '		-20	20	V
drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-150	mA
	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-95	mA
peak drain current	$T_{amb} = 25  ^{\circ}C$ ; single pulse; $t_p \le 10  \mu s$		-	-0.6	Α
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	mW
		[1]	-	310	mW
	T <sub>sp</sub> = 25 °C		-	830	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					
source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-150	mA
n rating					
electrostatic discharge voltage	HBM	[3]	-	1000	V
	drain-source voltage gate-source voltage drain current  peak drain current total power dissipation  junction temperature ambient temperature storage temperature diode source current rating	$ \begin{array}{lll} drain\text{-source voltage} & T_j = 25 \ ^\circ\text{C} \\ gate\text{-source voltage} \\ drain current & V_{GS} = -10 \ ^\circ\text{C}; \ T_{amb} = 25 \ ^\circ\text{C} \\ \hline V_{GS} = -10 \ ^\circ\text{C}; \ T_{amb} = 100 \ ^\circ\text{C} \\ \hline Peak drain current & T_{amb} = 25 \ ^\circ\text{C}; \ single \ pulse; \ t_p \leq 10 \ ^\mu\text{s} \\ \hline total \ power \ dissipation & T_{amb} = 25 \ ^\circ\text{C} \\ \hline Junction \ temperature & \\ ambient \ temperature & \\ storage \ temperature & \\ \hline storage \ temperature & \\ \hline source \ current & T_{amb} = 25 \ ^\circ\text{C} \\ \hline 1 \ rating & \hline \end{array} $	$ \begin{array}{c} drain\text{-source voltage} \\ gate\text{-source voltage} \\ drain current \\ \hline \\ V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C} \\ \hline \\ V_{GS} = -10 \text{ V}; T_{amb} = 100 \text{ °C} \\ \hline \\ 11 \\ \hline \\ peak drain current \\ \hline \\ T_{amb} = 25 \text{ °C}; single pulse; t_p \leq 10 \mu\text{s} \\ \hline \\ total power dissipation \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ 11 \\ \hline \\ T_{sp} = 25 \text{ °C} \\ \hline \\ junction temperature \\ \hline \\ ambient temperature \\ \hline \\ storage temperature \\ \hline \\ storage temperature \\ \hline \\ \\ source current \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ \hline \\ 11 \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ \hline \\ \hline \\ 11 \\ \hline \\ \hline \\ T_{amb} = 25 \text{ °C} \\ \hline \\ $	$ \begin{array}{c} drain\text{-source voltage} & T_{j} = 25  ^{\circ}\text{C} & -20 \\ gate\text{-source voltage} & V_{GS} = -10  \text{V};  T_{amb} = 25  ^{\circ}\text{C} & \boxed{11}  - \\ V_{GS} = -10  \text{V};  T_{amb} = 100  ^{\circ}\text{C} & \boxed{11}  - \\ Peak  drain  current & T_{amb} = 25  ^{\circ}\text{C};  single  pulse;  t_{p} \leq 10  \mu s & - \\ total  power  dissipation & T_{amb} = 25  ^{\circ}\text{C} & \boxed{11}  - \\ T_{sp} = 25  ^{\circ}\text{C} & \boxed{11}  - \\ T_{sp} = 25  ^{\circ}\text{C} & - \\ Junction  temperature & -55 \\ ambient  temperature & -55 \\ storage  temperature & -65 \\ \hline storage  temperature & -65 \\ \hline source  current & T_{amb} = 25  ^{\circ}\text{C} & \boxed{11}  - \\ \hline rating & -25  ^{\circ}\text{C} & \boxed{11}  - \\ \hline \end{array} $	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

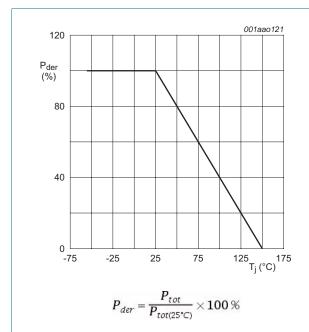


Fig 1. Normalized total power dissipation as a function of junction temperature

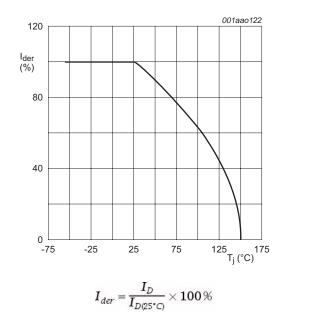
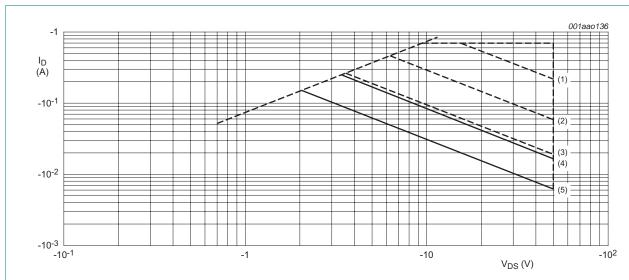


Fig 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> is single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3)  $t_p = 100 \text{ ms}$
- (4) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (5) DC;  $T_{amb} = 25$  °C; drain mounting pad 1 cm<sup>2</sup>

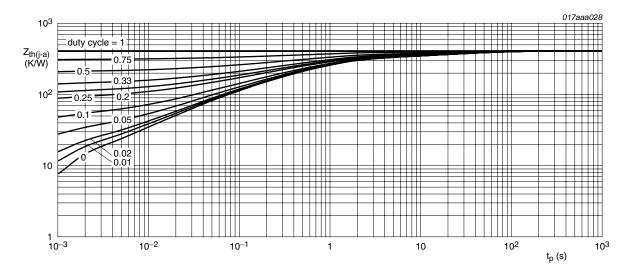
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

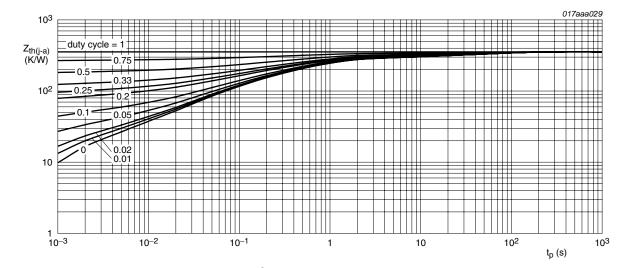
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	415	480	K/W
			[2]	-	350	400	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	150	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 7. Characteristics

Table 7. Characteristics

Table 1.	Onal acteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-50	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1.1	-1.6	-2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	4.5	7.5	Ω
	resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 150 \text{ °C}$	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	5.7	8.5	Ω
g <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -25 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	24	36	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -30 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -10 V;	-	13	26	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	48	96	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.48	-0.85	-1.2	V

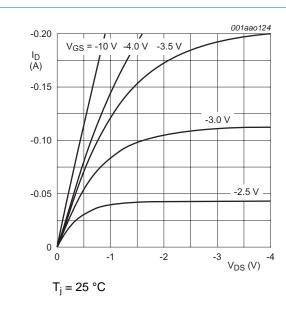
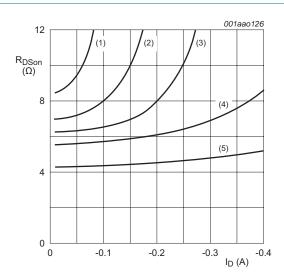


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



T<sub>i</sub> = 25 °C

(1)  $V_{GS} = -3.0 \text{ V}$ 

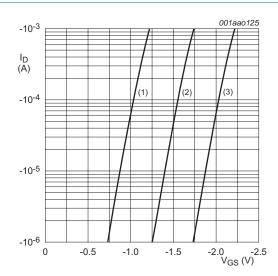
(2)  $V_{GS} = -3.5 \text{ V}$ 

(3)  $V_{GS} = -4.0 \text{ V}$ 

(4)  $V_{GS} = -5.0 \text{ V}$ 

(5)  $V_{GS} = -10.0 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



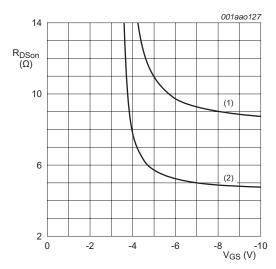
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

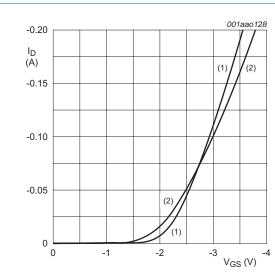


 $I_D = -200 \text{ mA}$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

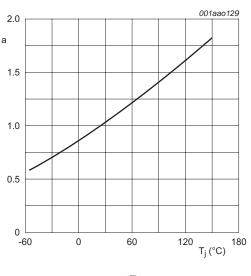


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

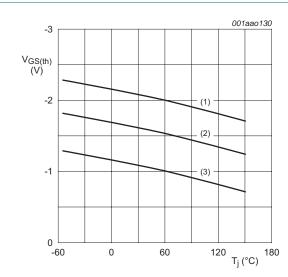
(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

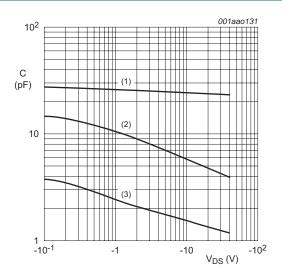
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

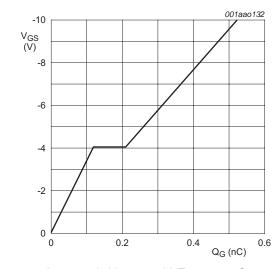


 $f = 1 MHz, V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 50 V, 150 mA P-channel Trench MOSFET



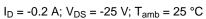


Fig 14. Gate-source voltage as a function of gate charge; typical values

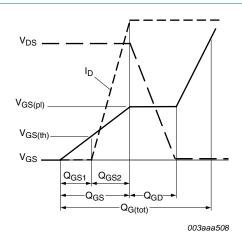
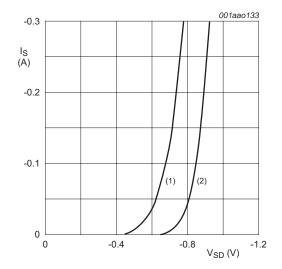


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

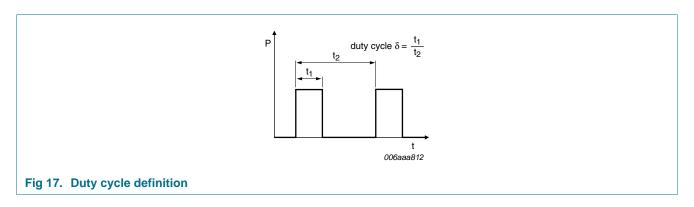
(1)  $T_j = 150 \, ^{\circ}\text{C}$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

50 V, 150 mA P-channel Trench MOSFET

#### 8. Test information



#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 9. Package outline

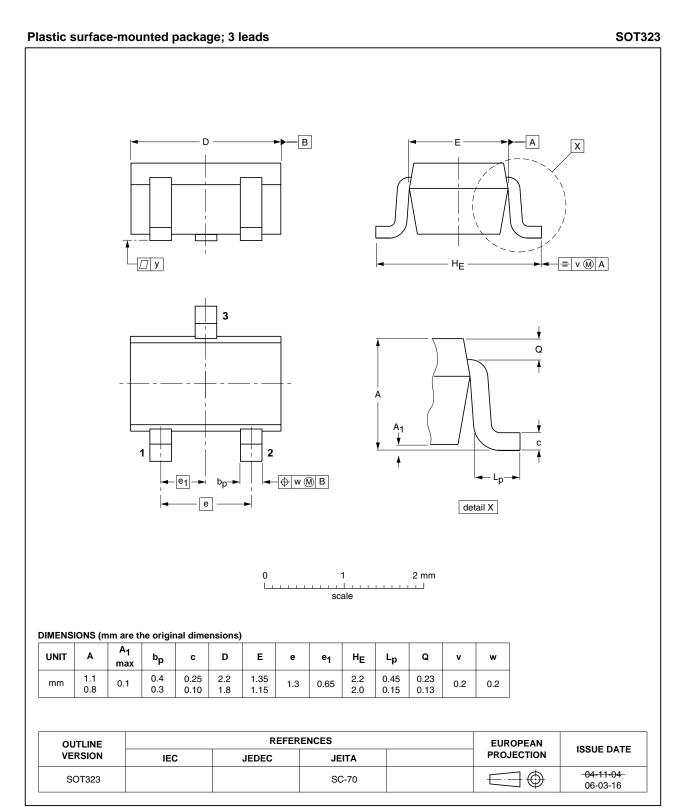
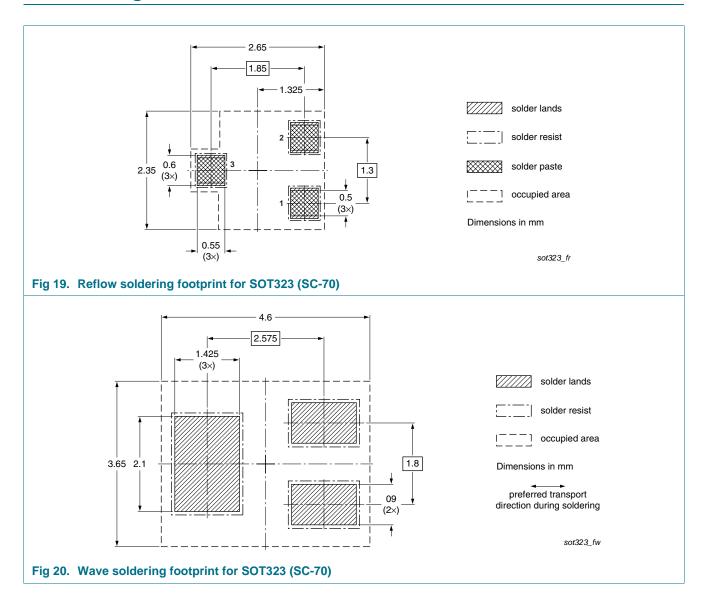


Fig 18. Package outline SOT323 (SC-70)

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#### 50 V, 150 mA P-channel Trench MOSFET

# 10. Soldering



50 V, 150 mA P-channel Trench MOSFET

# 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKW v.1	20110523	Product data sheet	-	-

#### 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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